

L Number	Hits	Search Text	DB	Time stamp
1	0	5286344.pn. and (semiconductor or chip or die or IC) and gate and passivation and (undop\$3 or dop\$3) with silicon	USPAT	2004/04/27 19:32
2	0	5286344.pn. and (semiconductor or chip or die or IC) and passivation and (undop\$3 or dop\$3) with silicon	USPAT	2004/04/27 19:32
3	1	5286344.pn. and (semiconductor or chip or die or IC) and (undop\$3 or dop\$3) with silicon	USPAT	2004/04/27 19:55
4	3	5202849.pn. or 5648175.pn. or 5948701.pn.	USPAT	2004/04/27 19:55
5	344	(semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG) (257/750 or 257/754 or 257/755) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG) (257/756 or 257/757 or 257/759) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG) (257/773 or 257/774 or 257/760) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 20:03
6	24	(257/750 or 257/754 or 257/755) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG) (257/756 or 257/757 or 257/759) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG) (257/773 or 257/774 or 257/760) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 20:04
7	11	(257/756 or 257/757 or 257/759) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG) (257/773 or 257/774 or 257/760) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 20:04
8	41	(257/773 or 257/774 or 257/760) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 and (((("Si" near "O.sub.2") or silicon near dioxide) with dop\$3 or BPSG or PSG or BSG)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 20:04
-	23	"5626716"	USPAT	2004/04/27 17:21
-	115	"5286344"	USPAT	2004/04/26 21:22
-	0	(semiconductor or die or chip or IC) and cap with ("Si.sub." near "N.sub.")	USPAT	2004/04/26 21:23
-	372	(semiconductor or die or chip or IC) and cap with ("Si.sub.3" near "N.sub.4")	USPAT	2004/04/26 21:23
-	1629	(semiconductor or die or chip or IC) and cap with ("Si.sub.3" near "N.sub.4") or silicon near nitride)	USPAT	2004/04/26 21:24
-	0	(semiconductor or die or chip or IC) and cap with ("Si.sub.3" near "N.sub.4") or silicon near nitride) with ("Si" near "O.sub.2")	USPAT	2004/04/26 21:24
-	213	(semiconductor or die or chip or IC) and cap with ("Si.sub.3" near "N.sub.4") or silicon near nitride) with ("Si" near "O.sub.2") or silicon near dioxide)	USPAT	2004/04/27 19:58
-	15	(semiconductor or die or chip or IC) and cap with ("Si.sub.3" near "N.sub.4") or silicon near nitride) with ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3	USPAT	2004/04/26 21:35
-	4	(semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) with (benefit or better) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3	USPAT	2004/04/26 21:36
-	0	(semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 with (benefit or better)	USPAT	2004/04/26 21:36
-	0	(semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 with (benefit or better or prodiv\$3)	USPAT	2004/04/26 21:36

-	0	(semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same (("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 with (benefit or better or prodiv\$3 or "for")	USPAT	2004/04/26 21:37
-	0	(semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same (("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 with (increas\$3)	USPAT	2004/04/26 21:37
-	391	(semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same (("Si" near "O.sub.2") or silicon near dioxide) with undop\$3	USPAT	2004/04/26 21:38
-	23	((semiconductor or die or chip or IC) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same (("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 ) and ("Si.sub.3" near "N.sub.4") or silicon near nitride) same (("Si" near "O.sub.2") or silicon near dioxide) with (increas\$3 or reduc\$3 or decreas\$3)	USPAT	2004/04/26 21:38
-	16	(semiconductor or die or chip or IC) and etch\$3 near stop\$4 with ("Si.sub.3" near "N.sub.4") or silicon near nitride) same (("Si" near "O.sub.2") or silicon near dioxide) with undop\$3	USPAT	2004/04/27 17:23
-	27	(semiconductor or die or chip or IC) and etch\$3 near stop\$4 same ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3	USPAT	2004/04/27 17:33
-	17	((semiconductor or die or chip or IC) and etch\$3 near stop\$4 same ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 ) and silicon near dioxide with dop\$3	USPAT	2004/04/27 17:34
-	35	(semiconductor or die or chip or IC) and etch\$3 with stop\$4 same ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3	USPAT	2004/04/27 17:37
-	22	((semiconductor or die or chip or IC) and etch\$3 with stop\$4 same ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 ) and silicon near dioxide with dop\$3	USPAT	2004/04/27 17:36
-	34	((semiconductor or die or chip or IC) and etch\$3 with stop\$4 same ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 ) and (silicon near dioxide with dop\$3 or BPSG or PSG or BSG)	USPAT	2004/04/27 17:37
-	26	(semiconductor or die or chip or IC) and etch\$3 with stop\$4 same ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 same (silicon near dioxide with dop\$3 or BPSG or PSG or BSG)	USPAT	2004/04/27 17:54
-	37	(semiconductor or die or chip or IC) and etch\$3 with (stop\$4 or mask\$3) same ("Si.sub.3" near "N.sub.4") or silicon near nitride) same ("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 same (silicon near dioxide with dop\$3 or BPSG or PSG or BSG)	USPAT	2004/04/27 18:06

-	11	((semiconductor or die or chip or IC) and etch\$3 with (stop\$4 or mask\$3) same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 same (silicon near dioxide with dop\$3 or BPSG or PSG or BSG) ) not ((semiconductor or die or chip or IC) and etch\$3 with stop\$4 same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 same (silicon near dioxide with dop\$3 or BPSG or PSG or BSG) )	USPAT	2004/04/27 17:55
-	37	(semiconductor or die or chip or IC) and etch\$3 with (stop\$4 or mask\$3) same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3) same (silicon near dioxide with dop\$3 or BPSG or PSG or BSG)	USPAT	2004/04/27 18:03
-	46	(semiconductor or die or chip or IC) and etch\$3 with (stop\$4 or mask\$3) same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3) and (silicon near dioxide with dop\$3 or BPSG or PSG or BSG)	USPAT	2004/04/27 18:10
-	20	((semiconductor or die or chip or IC) and etch\$3 with (stop\$4 or mask\$3) same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3) and (silicon near dioxide with dop\$3 or BPSG or PSG or BSG) ) not ((semiconductor or die or chip or IC) and etch\$3 with stop\$4 same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 same (silicon near dioxide with dop\$3 or BPSG or PSG or BSG) )	USPAT	2004/04/27 18:03
-	34	(semiconductor or die or chip or IC) and (etch\$3 with stop\$4 or "etch-stopping") same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3) and (silicon near dioxide with dop\$3 or BPSG or PSG or BSG)	USPAT	2004/04/27 18:11
-	8	((semiconductor or die or chip or IC) and (etch\$3 with stop\$4 or "etch-stopping") same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3) and (silicon near dioxide with dop\$3 or BPSG or PSG or BSG) ) not ((semiconductor or die or chip or IC) and etch\$3 with stop\$4 same ((("Si.sub.3" near "N.sub.4") or silicon near nitride) same ((("Si" near "O.sub.2") or silicon near dioxide) with undop\$3 same (silicon near dioxide with dop\$3 or BPSG or PSG or BSG) )	USPAT	2004/04/27 18:11